

**SANYO**

No.4635

**2SK1840**

N-Channel Enhancement MOS Silicon FET

Analog Switch Applications

**Features**

- Large  $|Y_{fs}|$ .
- Enhancement type.
- Low ON resistance.

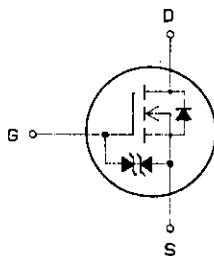
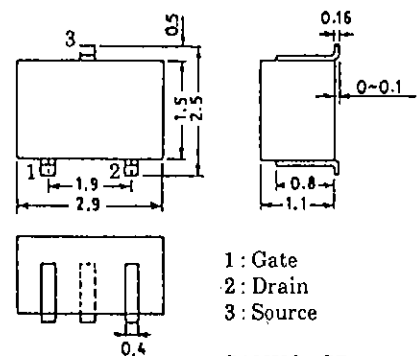
**Absolute Maximum Ratings at  $T_a = 25^\circ\text{C}$** 

			unit
Drain-to-Source Voltage	$V_{DSS}$	30	V
Gate-to-Source Voltage	$V_{GSS}$	$\pm 12$	V
Drain Current(DC)	$I_D$	100	mA
Drain Current(Pulse)	$I_{DP}$	300	mA
Allowable Power Dissipation	$P_D$	200	mW
Channel Temperature	$T_{ch}$	125	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

**Electrical Characteristics at  $T_a = 25^\circ\text{C}$** 

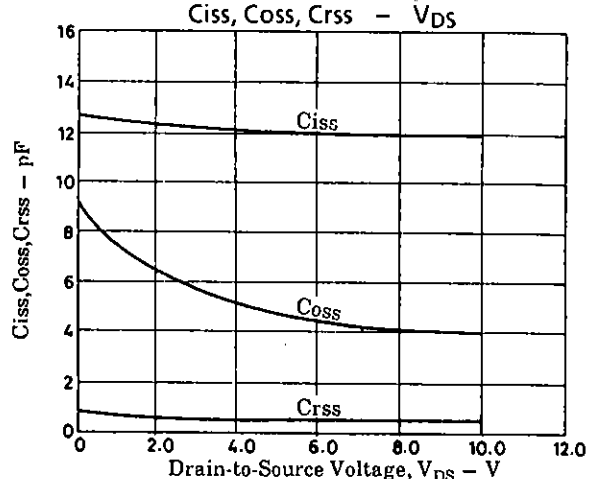
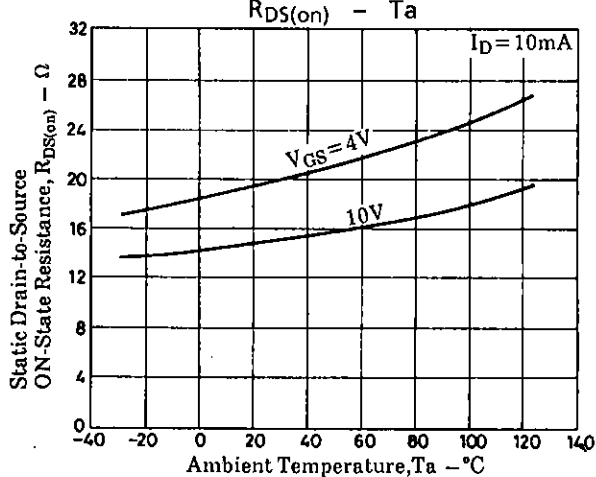
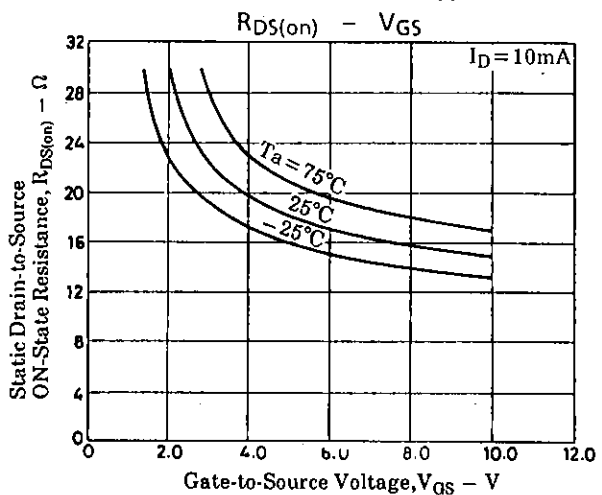
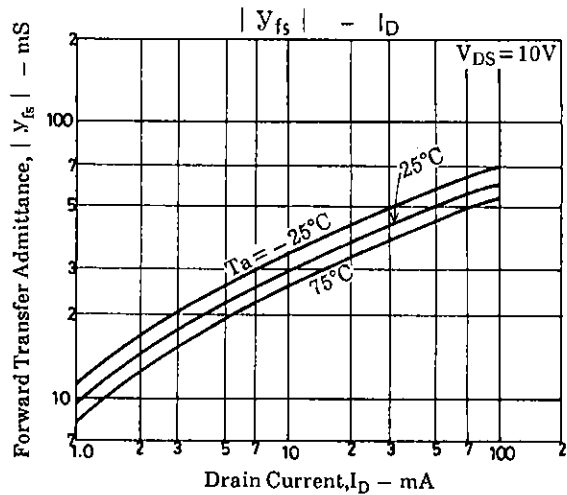
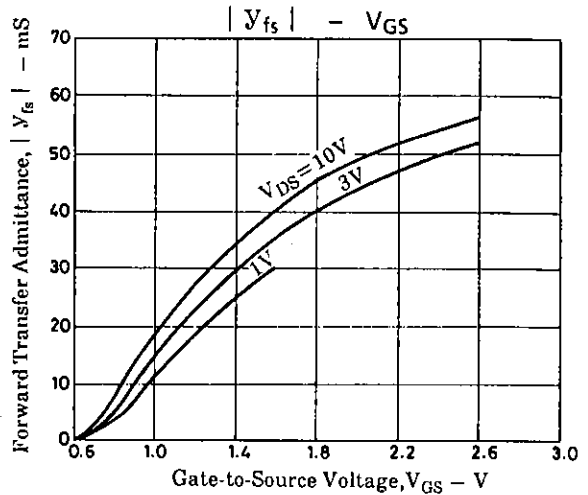
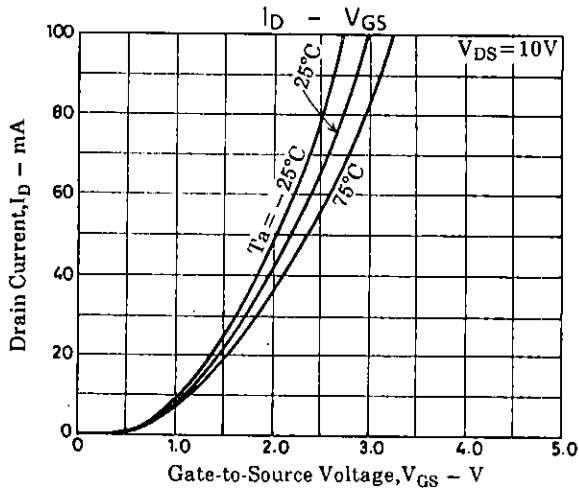
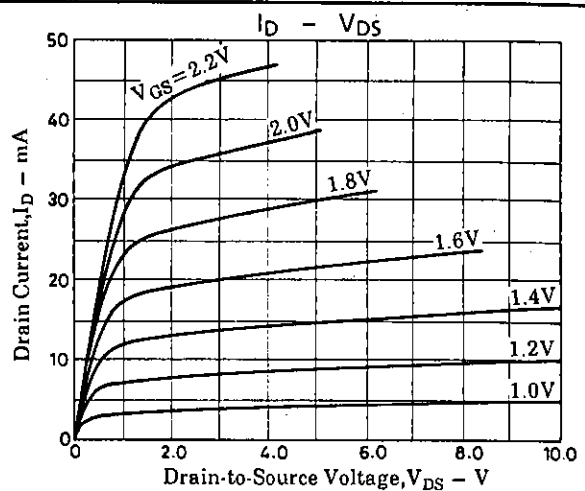
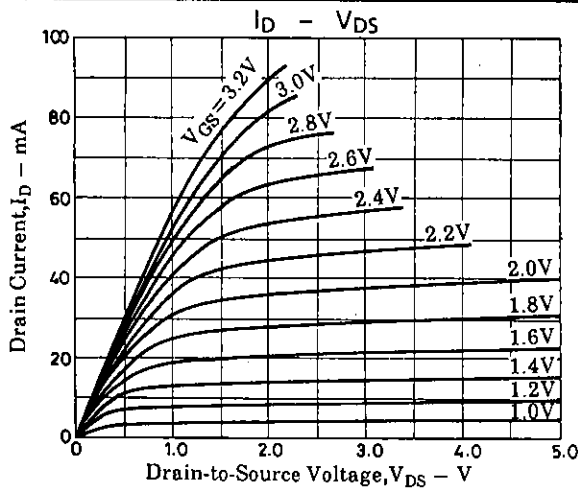
			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 10\mu\text{A}, V_{GS} = 0$	30			V
Drain Current	$I_{DSS}$	$V_{DS} = 15\text{V}, V_{GS} = 0$			1	$\mu\text{A}$
Gate Cutoff Current	$I_{GSS}$	$V_{GS} = \pm 10\text{V}, V_{DS} = 0$		0.01	$\pm 10$	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10\text{V}, I_D = 100\mu\text{A}$	0.3	0.9	1.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, I_D = 50\text{mA}, f = 1\text{kHz}$	25	50		mS
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 10\text{mA}$		15	25	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$		12		pF
Output Capacitance	$C_{oss}$	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$		4		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$		0.4		pF

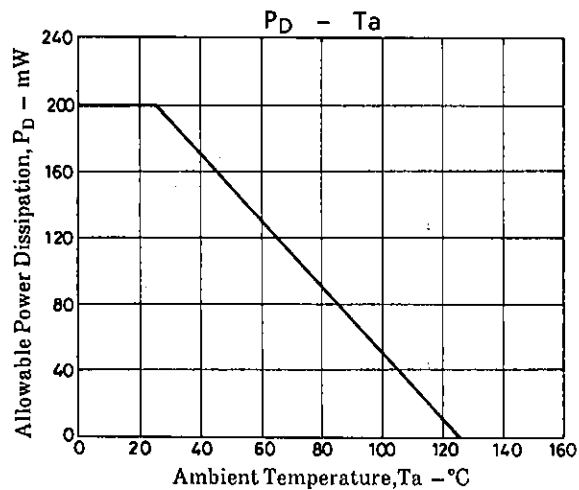
Marking: JJ

**Electrical Connection****Package Dimensions 2024B**  
(unit: mm)

SANYO:CP

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